Michael J Manfra

List of Publications by Year in Descending Order

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167	4,525	36	61
papers	citations	h-index	g-index
178	5,756	7.2	5.64
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
167	Domain Textures in the Fractional Quantum Hall Effect.. *Physical Review Letters*, **2022**, 128, 017401	7.4	0
166	Impact of bulk-edge coupling on observation of anyonic braiding statistics in quantum Hall interferometers.. *Nature Communications*, **2022**, 13, 344	17.4	0
165	Effect of Rashba and Dresselhaus spin-orbit coupling on supercurrent rectification and magnetochiral anisotropy of ballistic Josephson junctions.. *Journal of Physics Condensed Matter*, **2022**,	1.8	3
164	Measurements of cyclotron resonance of the interfacial states in strong spin-orbit coupled 2D electron gases proximitized with aluminum. *Applied Physics Letters*, **2022**, 120, 142105	3.4	0
163	InSbAs Two-Dimensional Electron Gases as a Platform for Topological Superconductivity. *Nano Letters*, **2021**, 21, 9990-9996	11.5	3
162	Supercurrent rectification and magnetochiral effects in symmetric Josephson junctions. *Nature Nanotechnology*, **2021**,	28.7	11
161	Simultaneous Operations in a Two-Dimensional Array of Singlet-Triplet Qubits. *PRX Quantum*, **2021**, 2,	6.1	3
160	Josephson junctions via anodization of epitaxial Al on an InAs heterostructure. *Applied Physics Letters*, **2021**, 119, 172601	3.4	1
159	Band Structure Extraction at Hybrid Narrow-Gap Semiconductor-Metal Interfaces. *Advanced Science* , **2021**, 8, 2003087	13.6	6
158	Observation of Flat Bands in Gated Semiconductor Artificial Graphene. *Physical Review Letters*, **2021**, 126, 106402	7.4	1
157	Floquet-enhanced spin swaps. *Nature Communications*, **2021**, 12, 2142	17.4	7
156	Adiabatic quantum state transfer in a semiconductor quantum-dot spin chain. *Nature Communications*, **2021**, 12, 2156	17.4	8
155	A cryogenic CMOS chip for generating control signals for multiple qubits. *Nature Electronics*, **2021**, 4, 64-70	28.4	29
154	Josephson Inductance as a Probe for Highly Ballistic Semiconductor-Superconductor Weak Links. *Physical Review Letters*, **2021**, 126, 037001	7.4	5
153	Anodic oxidation of epitaxial superconductor-semiconductor hybrids. *Physical Review Materials*, **2021**, 5,	3.2	2
152	Hydrodynamic and Ballistic Transport over Large Length Scales in GaAs/AlGaAs. *Physical Review Letters*, **2021**, 126, 076803	7.4	6
151	Precision measurement of electron-electron scattering in GaAs/AlGaAs using transverse magnetic focusing. *Nature Communications*, **2021**, 12, 5048	17.4	0

150	Overcoming anomalous suppression of m-plane AlGaN growth by molecular-beam epitaxy using indium as a surfactant. *Journal of Applied Physics*, **2021**, 130, 105702	2.5	0
149	Mid-infrared intersubband absorption in strain-balanced non-polar (In)AlGaN/InGaN multi-quantum wells. *Optical Materials Express*, **2021**, 11, 3284	2.6	2
148	Long-Distance Superexchange between Semiconductor Quantum-Dot Electron Spins. *Physical Review Letters*, **2021**, 126, 017701	7.4	5
147	Photoluminescence study of non-polar m-plane InGaN and nearly strain-balanced InGaN/AlGaN superlattices. *Journal of Applied Physics*, **2020**, 127, 185702	2.5	6
146	Conditional teleportation of quantum-dot spin states. *Nature Communications*, **2020**, 11, 3022	17.4	11
145	Relating Andreev Bound States and Supercurrents in Hybrid Josephson Junctions. *Physical Review Letters*, **2020**, 124, 226801	7.4	7
144	Topological superconductivity in hybrid devices. *Nature Physics*, **2020**, 16, 718-724	16.2	30
143	Coherent Multispin Exchange Coupling in a Quantum-Dot Spin Chain. *Physical Review X*, **2020**, 10,	9.1	8
142	Coherent transport through a Majorana island in an Aharonov-Bohm interferometer. *Nature Communications*, **2020**, 11, 3212	17.4	15
141	The dependence of aluminum lattice orientation on semiconductor lattice parameter in planar InAs/Al hybrid heterostructures. *Journal of Crystal Growth*, **2020**, 535, 125570	1.6	
140	Anomalous Nematic States in High Half-Filled Landau Levels. *Physical Review Letters*, **2020**, 124, 067601	7.4	4
139	Quantum Dots in an InSb Two-Dimensional Electron Gas. *Physical Review Applied*, **2020**, 13,	4.3	5
138	Accurate characterization of tip-induced potential using electron interferometry. *Applied Physics Letters*, **2020**, 117, 193101	3.4	0
137	Repairing the surface of InAs-based topological heterostructures. *Journal of Applied Physics*, **2020**, 128, 114301	2.5	5
136	Observation of Photoinduced Terahertz Gain in GaAs Quantum Wells: Evidence for Radiative Two-Exciton-to-Biexciton Scattering. *Physical Review Letters*, **2020**, 125, 167401	7.4	1
135	Reduction of charge noise in shallow GaAs/AlGaAs heterostructures with insulated gates. *Applied Physics Letters*, **2020**, 117, 133504	3.4	3
134	Direct observation of anyonic braiding statistics. *Nature Physics*, **2020**, 16, 931-936	16.2	61
133	Indium surfactant assisted epitaxy of non-polar (10 1 ▯0) AlGaN/InGaN multiple quantum well heterostructures. *Journal of Applied Physics*, **2020**, 128, 115701	2.5	5

132	Hidden Quantum Hall Stripes in Al_{x}Ga_{1-x}As/Al_{0.24}Ga_{0.76}As Quantum Wells. *Physical Review Letters*, **2020**, 125, 236803	7.4	0
131	Gate-defined quantum point contact in an InAs two-dimensional electron gas. *Physical Review B*, **2019**, 100,	3.3	7
130	Coherent spin-state transfer via Heisenberg exchange. *Nature*, **2019**, 573, 553-557	50.4	39
129	Electron bubbles and the structure of the orbital wave function. *Physical Review B*, **2019**, 99,	3.3	5
128	Evidence of topological superconductivity in planar Josephson junctions. *Nature*, **2019**, 569, 89-92	50.4	121
127	Aharonov�Bohm interference of fractional quantum Hall edge modes. *Nature Physics*, **2019**, 15, 563-569	16.2	40
126	Fast spin exchange across a multielectron mediator. *Nature Communications*, **2019**, 10, 1196	17.4	25
125	Observation of new plasmons in the fractional quantum Hall effect: Interplay of topological and nematic orders. *Science Advances*, **2019**, 5, eaav3407	14.3	5
124	Integrated high electron mobility transistors in GaAs/AlGaAs heterostructures for amplification at sub-Kelvin temperatures. *Applied Physics Letters*, **2019**, 114, 053104	3.4	3
123	Ballistic superconductivity and tunable �junctions in InSb quantum wells. *Nature Communications*, **2019**, 10, 3764	17.4	17
122	Topological kink plasmons on magnetic-domain boundaries. *Nature Communications*, **2019**, 10, 4565	17.4	7
121	The Effect of the Ion Beam Energy on M-plane InGaN Layer Preparation for STEM. *Microscopy and Microanalysis*, **2019**, 25, 1702-1703	0.5	
120	Toward durable Al-InSb hybrid heterostructures via epitaxy of 2ML interfacial InAs screening layers. *Physical Review Materials*, **2019**, 3,	3.2	4
119	Resistivity anisotropy of quantum Hall stripe phases. *Physical Review B*, **2019**, 100,	3.3	4
118	Impact of growth conditions and strain on indium incorporation in non-polar m-plane (101�0) InGaN grown by plasma-assisted molecular beam epitaxy. *APL Materials*, **2019**, 7, 121109	5.7	9
117	Vacuum Bloch�Siegert shift in Landau polaritons with ultra-high cooperativity. *Nature Photonics*, **2018**, 12, 324-329	33.9	52
116	Optimization of edge state velocity in the integer quantum Hall regime. *Physical Review B*, **2018**, 97,	3.3	7
115	h/e Superconducting Quantum Interference through Trivial Edge States in InAs. *Physical Review Letters*, **2018**, 120, 047702	7.4	19

114	Kinetic instability of AlGaN alloys during MBE growth under metal-rich conditions on m-plane GaN miscut towards the -c axis. *Journal of Applied Physics*, **2018**, 123, 161581	2.5	10
113	Spin of a Multielectron Quantum Dot and Its Interaction with a Neighboring Electron. *Physical Review X*, **2018**, 8,	9.1	13
112	Superconducting gatemon qubit based on a proximitized two-dimensional electron gas. *Nature Nanotechnology*, **2018**, 13, 915-919	28.7	68
111	Emerging many-body effects in semiconductor artificial graphene with low disorder. *Nature Communications*, **2018**, 9, 3299	17.4	13
110	Direct entropy measurement in a mesoscopic quantum system. *Nature Physics*, **2018**, 14, 1083-1086	16.2	25
109	Electron-electron interactions and the paired-to-nematic quantum phase transition in the second Landau level. *Nature Communications*, **2018**, 9, 2400	17.4	15
108	High-mobility InAs 2DEGs on GaSb substrates: A platform for mesoscopic quantum transport. *Physical Review Materials*, **2018**, 2,	3.2	14
107	Observation of Dirac bands in artificial graphene in small-period nanopatterned GaAs quantum wells. *Nature Nanotechnology*, **2018**, 13, 29-33	28.7	31
106	Effect of illumination on quantum lifetime in GaAs quantum wells. *Physical Review B*, **2018**, 98,	3.3	4
105	Hybridization of Subgap States in One-Dimensional Superconductor-Semiconductor Coulomb Islands. *Physical Review Letters*, **2018**, 121, 256803	7.4	15
104	A capacitance spectroscopy-based platform for realizing gate-defined electronic lattices. *Journal of Applied Physics*, **2018**, 124, 124305	2.5	
103	Effect of density on microwave-induced resistance oscillations in back-gated GaAs quantum wells. *Physical Review B*, **2018**, 98,	3.3	1
102	Readout of singlet-triplet qubits at large magnetic field gradients. *Physical Review B*, **2018**, 98,	3.3	17
101	Intersubband Transitions in Nonpolar m-Plane AlGaN/GaN Heterostructures. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1700828	1.6	7
100	Giant Spin-Orbit Splitting in Inverted InAs/GaSb Double Quantum Wells. *Physical Review Letters*, **2017**, 118, 016801	7.4	23
99	Quantum lifetime in ultrahigh quality GaAs quantum wells: Relationship to 5/2 and impact of density fluctuations. *Physical Review B*, **2017**, 96,	3.3	14
98	Scaling of Majorana Zero-Bias Conductance Peaks. *Physical Review Letters*, **2017**, 119, 136803	7.4	221
97	Effect of density on quantum Hall stripe orientation in tilted magnetic fields. *Physical Review B*, **2017**, 95,	3.3	9

96	Apparent temperature-induced reorientation of quantum Hall stripes. *Physical Review B*, **2017**, 95,	3.3	6
95	Microwave-induced resistance oscillations in a back-gated GaAs quantum well. *Physical Review B*, **2017**, 95,	3.3	15
94	High-temperature resistivity measured at □52 as a predictor of the two-dimensional electron gas quality in the N=1 Landau level. *Physical Review B*, **2017**, 95,	3.3	4
93	High-fidelity entangling gate for double-quantum-dot spin qubits. *Npj Quantum Information*, **2017**, 3,	8.6	120
92	Symmetric operation of the resonant exchange qubit. *Physical Review B*, **2017**, 96,	3.3	21
91	Spin-orbit interaction in a dual gated InAs/GaSb quantum well. *Physical Review B*, **2017**, 96,	3.3	23
90	Possible nematic to smectic phase transition in a two-dimensional electron gas at half-filling. *Nature Communications*, **2017**, 8, 1536	17.4	17
89	Negative Spin Exchange in a Multielectron Quantum Dot. *Physical Review Letters*, **2017**, 119, 227701	7.4	14
88	Onset of quantum criticality in the topological-to-nematic transition in a two-dimensional electron gas at filling factor □5/2. *Physical Review B*, **2017**, 96,	3.3	14
87	Notch filtering the nuclear environment of a spin qubit. *Nature Nanotechnology*, **2017**, 12, 16-20	28.7	55
86	Spectrum of the Nuclear Environment for GaAs Spin Qubits. *Physical Review Letters*, **2017**, 118, 177702	7.4	40
85	Mobility in excess of 106 cm2/V s in InAs quantum wells grown on lattice mismatched InP substrates. *Applied Physics Letters*, **2017**, 111, 142106	3.4	12
84	Collective non-perturbative coupling of 2D electrons with high-quality-factor terahertz cavity photons. *Nature Physics*, **2016**, 12, 1005-1011	16.2	110
83	Decoupling Edge Versus Bulk Conductance in the Trivial Regime of an InAs/GaSb Double Quantum Well Using Corbino Ring Geometry. *Physical Review Letters*, **2016**, 117, 077701	7.4	30
82	Reorientation of quantum Hall stripes within a partially filled Landau level. *Physical Review B*, **2016**, 93,	3.3	20
81	Optical Emission Spectroscopy Study of Competing Phases of Electrons in the Second Landau Level. *Physical Review Letters*, **2016**, 116, 016801	7.4	11
80	Evidence for a new symmetry breaking mechanism reorienting quantum Hall nematics. *Physical Review B*, **2016**, 93,	3.3	16
79	Resistively detected high-order magnetoplasmons in a high-quality two-dimensional electron gas. *Physical Review B*, **2016**, 93,	3.3	4

78	Noise Suppression Using Symmetric Exchange Gates in Spin Qubits. *Physical Review Letters*, **2016**, 116, 116801	7.4	145
77	Stability of High-Density Two-Dimensional Excitons against a Mott Transition in High Magnetic Fields Probed by Coherent Terahertz Spectroscopy. *Physical Review Letters*, **2016**, 117, 207402	7.4	7
76	Quantized Conductance and Large g-Factor Anisotropy in InSb Quantum Point Contacts. *Nano Letters*, **2016**, 16, 7509-7513	11.5	31
75	Modified MBE hardware and techniques and role of gallium purity for attainment of two dimensional electron gas mobility >35□06 cm2/V s in AlGaAs/GaAs quantum wells grown by MBE. *Journal of Crystal Growth*, **2016**, 441, 71-77	1.6	40
74	Observation of a transition from a topologically ordered to a spontaneously broken symmetry phase. *Nature Physics*, **2016**, 12, 191-195	16.2	56
73	Dramatic enhancement of near-infrared intersubband absorption in c-plane AlInN/GaN superlattices. *Applied Physics Letters*, **2016**, 108, 121108	3.4	7
72	Quasi-ballistic thermal transport in Al0.1Ga0.9N thin film semiconductors. *Applied Physics Letters*, **2016**, 109, 243107	3.4	18
71	Observation of electron states of small period artificial graphene in nano-patterned GaAs quantum wells. *Applied Physics Letters*, **2016**, 109, 113101	3.4	7
70	Electron-Hole Asymmetric Chiral Breakdown of Reentrant Quantum Hall States. *Physical Review Letters*, **2016**, 117, 166805	7.4	6
69	Electric and Magnetic Tuning Between the Trivial and Topological Phases in InAs/GaSb Double Quantum Wells. *Physical Review Letters*, **2015**, 115, 036803	7.4	66
68	Induced superconductivity in high-mobility two-dimensional electron gas in gallium arsenide heterostructures. *Nature Communications*, **2015**, 6, 7426	17.4	71
67	Transport of a sliding Wigner crystal in the four flux composite fermion regime. *Physical Review B*, **2015**, 92,	3.3	9
66	Shubnikov□e Haas oscillations in a two-dimensional electron gas under subterahertz radiation. *Physical Review B*, **2015**, 92,	3.3	11
65	Gapped excitations of unconventional fractional quantum Hall effect states in the second Landau level. *Physical Review B*, **2015**, 92,	3.3	6
64	Coherent vertical electron transport and interface roughness effects in AlGaN/GaN intersubband devices. *Journal of Applied Physics*, **2015**, 118, 224308	2.5	19
63	In-surface confinement of topological insulator nanowire surface states. *Applied Physics Letters*, **2015**, 107, 121605	3.4	13
62	Gate-tunable high mobility remote-doped InSb/In1⊠AlxSb quantum well heterostructures. *Applied Physics Letters*, **2015**, 106, 142103	3.4	24
61	Surface topography and chemistry shape cellular behavior on wide band-gap semiconductors. *Acta Biomaterialia*, **2014**, 10, 2455-62	10.8	21

60	Molecular Beam Epitaxy of Ultra-High-Quality AlGaAs/GaAs Heterostructures: Enabling Physics in Low-Dimensional Electronic Systems. *Annual Review of Condensed Matter Physics*, **2014**, 5, 347-373	19.7	81
59	Field-effect-induced two-dimensional electron gas utilizing modulation-doped ohmic contacts. *Solid State Communications*, **2014**, 197, 20-24	1.6	5
58	Multiphoton processes at cyclotron resonance subharmonics in a two-dimensional electron system under dc and microwave excitation. *Physical Review B*, **2014**, 90,	3.3	7
57	Superradiant decay of cyclotron resonance of two-dimensional electron gases. *Physical Review Letters*, **2014**, 113, 047601	7.4	68
56	Low-temperature illumination and annealing of ultrahigh quality quantum wells. *Physical Review B*, **2014**, 90,	3.3	15
55	□5/2 fractional quantum Hall state in the presence of alloy disorder. *Physical Review Letters*, **2014**, 112, 116804	7.4	28
54	Full control of quadruple quantum dot circuit charge states in the single electron regime. *Applied Physics Letters*, **2014**, 104, 183111	3.4	35
53	Impact of short-range scattering on the metallic transport of strongly correlated two-dimensional holes in GaAs quantum wells. *Physical Review B*, **2014**, 90,	3.3	1
52	Homogeneous AlGaN/GaN superlattices grown on free-standing (11□00) GaN substrates by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2013**, 103, 232103	3.4	19
51	Comparative study of intersubband absorption in AlGaN/GaN and AlInN/GaN superlattices: Impact of material inhomogeneities. *Physical Review B*, **2013**, 88,	3.3	25
50	Strong heavy-to-light hole intersubband absorption in the valence band of carbon-doped GaAs/AlAs superlattices. *Journal of Applied Physics*, **2013**, 113, 053103	2.5	1
49	Effects of forming gas anneal on ultrathin InGaAs nanowire metal-oxide-semiconductor field-effect transistors. *Applied Physics Letters*, **2013**, 102, 093505	3.4	21
48	Heavy-to-light hole intersubband absorption in the valence band of GaAs/AlAs heterostructures. *Materials Research Society Symposia Proceedings*, **2013**, 1509, 1		
47	Evidence for effective mass reduction in GaAs/AlGaAs quantum wells. *Physical Review B*, **2013**, 87,	3.3	30
46	Growth and electrical characterization of Al0.24Ga0.76As/AlxGa1□As/Al0.24Ga0.76As modulation-doped quantum wells with extremely low x. *Applied Physics Letters*, **2013**, 102, 252103	3.4	11
45	20□80nm Channel length InGaAs gate-all-around nanowire MOSFETs with EOT=1.2nm and lowest SS=63mV/dec **2012**,		16
44	Magnetoplasmon resonance in a two-dimensional electron system driven into a zero-resistance state. *Physical Review B*, **2012**, 85,	3.3	12
43	Repeatable low-temperature negative-differential resistance from Al0.18Ga0.82N/GaN resonant tunneling diodes grown by molecular-beam epitaxy on free-standing GaN substrates. *Applied Physics Letters*, **2012**, 100, 252105	3.4	54

42	III-V gate-all-around nanowire MOSFET process technology: From 3D to 4D **2012**,		24
41	Near-Infrared Absorption in Lattice-Matched AlInN/GaN and Strained AlGaN/GaN Heterostructures Grown by MBE on Low-Defect GaN Substrates. *Journal of Electronic Materials*, **2012**, 41, 881-886	1.9	17
40	Millimeter wave transmission spectroscopy of gated two-dimensional hole systems. *Applied Physics Letters*, **2012**, 100, 192104	3.4	3
39	Improvement of near-infrared absorption linewidth in AlGaN/GaN superlattices by optimization of delta-doping location. *Applied Physics Letters*, **2012**, 101, 102104	3.4	28
38	Contrasting energy scales of reentrant integer quantum Hall states. *Physical Review B*, **2012**, 86,	3.3	33
37	Exploration of the limits to mobility in two-dimensional hole systems in GaAs/AlGaAs quantum wells. *Physical Review B*, **2012**, 85,	3.3	12
36	Free standing GaN nano membrane by laser lift-off method. *Materials Research Society Symposia Proceedings*, **2012**, 1432, 53		4
35	Effect of strain on stripe phases in the quantum Hall regime. *Physical Review Letters*, **2011**, 106, 016804	7.4	43
34	Particle-hole asymmetry of fractional quantum Hall states in the second Landau level of a two-dimensional hole system. *Physical Review B*, **2011**, 83,	3.3	7
33	Scattering mechanisms in a high-mobility low-density carbon-doped (100) GaAs two-dimensional hole system. *Physical Review B*, **2011**, 83,	3.3	9
32	Quantitative analysis of the disorder broadening and the intrinsic gap for the □52 fractional quantum Hall state. *Physical Review B*, **2011**, 84,	3.3	35
31	Nonconventional odd-denominator fractional quantum Hall states in the second Landau level. *Physical Review Letters*, **2010**, 105, 246808	7.4	90
30	Magnetotransport in Zener tunneling regime in a high-mobility two-dimensional hole gas. *Physical Review B*, **2009**, 80,	3.3	9
29	Near-infrared intersubband absorption in molecular-beam epitaxy-grown lattice-matched InAlN/GaN superlattices. *Applied Physics Letters*, **2009**, 94, 161111	3.4	29
28	Cyclotron mass of two-dimensional holes in (100) oriented GaAs□AlGaAs heterostructures. *Applied Physics Letters*, **2008**, 92, 012109	3.4	13
27	Transport and percolation in a low-density high-mobility two-dimensional hole system. *Physical Review Letters*, **2007**, 99, 236402	7.4	54
26	Mesoscopic structures and two-dimensional hole systems in fully field effect controlled heterostructures. *Applied Physics Letters*, **2007**, 91, 033510	3.4	6
25	Impact of spin-orbit coupling on quantum Hall nematic phases. *Physical Review Letters*, **2007**, 98, 206804	7.4	22

24	High-reflectivity ultraviolet AlGaN/AlGaN distributed Bragg reflectors. *Applied Physics Letters*, **2006**, 88, 171101	3.4	32
23	Quantum transport in high mobility AlGaN/GaN 2DEGs and nanostructures. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1706-1712	1.3	15
22	High mobility two-dimensional hole system in GaAs/AlGaAs quantum wells grown on (100) GaAs substrates. *Applied Physics Letters*, **2005**, 86, 162106	3.4	39
21	Acoustic phonon scattering in a low density, high mobility AlGaN/GaN field-effect transistor. *Applied Physics Letters*, **2005**, 86, 252108	3.4	40
20	Electron mobility exceeding 160000cm2/Vs in AlGaN/GaN heterostructures grown by molecular-beam epitaxy. *Applied Physics Letters*, **2004**, 85, 5394-5396	3.4	51
19	Quantum and transport lifetimes in a tunable low-density AlGaN/GaN two-dimensional electron gas. *Applied Physics Letters*, **2004**, 85, 5278-5280	3.4	26
18	Dynamics of trapped charge in GaN/AlGaN/GaN high electron mobility transistors grown by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2004**, 84, 422-424	3.4	47
17	LARGE CYCLOTRON-RESONANCE LINE SPLITTING OF TWO-DIMENSIONAL ELECTRONS IN AlGaN/GaN AND AlGaAs/GaAs HETEROSTRUCTURES. *International Journal of Modern Physics B*, **2004**, 18, 3761-3768	1.1	2
16	Electron scattering in AlGaN/GaN structures. *Applied Physics Letters*, **2004**, 84, 1507-1509	3.4	40
15	Poole-Frenkel electron emission from the traps in AlGaN/GaN transistors. *Journal of Applied Physics* , **2004**, 95, 6414-6419	2.5	149
14	Electron mobility in very low density GaN/AlGaN/GaN heterostructures. *Applied Physics Letters*, **2004** , 85, 1722-1724	3.4	41
13	Mechanisms of gate lag in GaN/AlGaN/GaN high electron mobility transistors. *Superlattices and Microstructures*, **2003**, 34, 33-53	2.8	83
12	High power GaN/AlGaN/GaN HEMTs operating at 2 to 25 GHz grown by plasma-assisted MBE. *Physica Status Solidi A*, **2003**, 200, 175-178		4
11	Nonparabolicity of the conduction band of wurtzite GaN. *Applied Physics Letters*, **2003**, 83, 4553-4555	3.4	32
10	Impact of Si doping on radio frequency dispersion in unpassivated GaN/AlGaN/GaN high-electron-mobility transistors grown by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2003**, 82, 4361-4363	3.4	45
9	Effect of dislocations on local transconductance in AlGaN/GaN heterostructures as imaged by scanning gate microscopy. *Applied Physics Letters*, **2003**, 83, 4559-4561	3.4	8
8	Dislocation and morphology control during molecular-beam epitaxy of AlGaN/GaN heterostructures directly on sapphire substrates. *Applied Physics Letters*, **2002**, 81, 1456-1458	3.4	34
7	High mobility AlGaN/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on semi-insulating GaN templates prepared by hydride vapor phase epitaxy. *Journal of Applied Physics*, **2002**, 92, 338-345	2.5	66

6	Direct imaging of reverse-bias leakage through pure screw dislocations in GaN films grown by molecular beam epitaxy on GaN templates. *Applied Physics Letters*, **2002**, 81, 79-81	3.4	247
5	Surface morphology and electronic properties of dislocations in AlGaN/GaN heterostructures. *Journal of Electronic Materials*, **2001**, 30, 110-114	1.9	15
4	Inhomogeneous spatial distribution of reverse bias leakage in GaN Schottky diodes. *Applied Physics Letters*, **2001**, 78, 1685-1687	3.4	246
3	Effect of growth stoichiometry on the electrical activity of screw dislocations in GaN films grown by molecular-beam epitaxy. *Applied Physics Letters*, **2001**, 78, 3980-3982	3.4	104
2	High-mobility AlGaN/GaN heterostructures grown by molecular-beam epitaxy on GaN templates prepared by hydride vapor phase epitaxy. *Applied Physics Letters*, **2000**, 77, 2888-2890	3.4	84
1	Photoluminescence Study of Carrier Localization and Recombination in Nearly Strain-Balanced Nonpolar InGaN/AlGaN Quantum Wells. *Physica Status Solidi (B): Basic Research*,2100569	1.3	